

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	1602	(semiconductor or die or chip or Ic) and (dielectric or insulat\$3) and (copper or "Cu") with (plug or via or interconnect\$3 or hole) and barrier and electroplat\$3	USPAT	OR	OFF	2005/03/30 16:58
S2	553	(semiconductor or die or chip or Ic) and (dielectric or insulat\$3) same etch\$3 same (copper or "Cu") with (plug or via or interconnect\$3 or hole) and barrier and electroplat\$3	USPAT	OR	OFF	2004/10/14 16:14
S3	9	"6441492".pn. or "6368484".pn. or "6339258".pn. or "6333560".pn. or "5865984".pn. or "5486282".pn. or "6375693".pn. or "6503834".pn. or "6731004".pn.	USPAT	OR	OFF	2004/10/14 15:47
S4	1252	(semiconductor or die or chip or Ic) and (dielectric or insulat\$3) and (copper or "Cu") with (plug or via or interconnect\$3 or hole) and barrier and electroplat\$3 and etch\$3 same (copper or "Cu")	USPAT	OR	OFF	2004/10/14 16:15
S5	283	(semiconductor or die or chip or Ic) and (dielectric or insulat\$3) and (copper or "Cu") with (plug or via or interconnect\$3 or hole) and barrier and electroplat\$3 and etch\$3 near (copper or "Cu")	USPAT	OR	OFF	2004/10/14 16:15
S6	4121	damas\$4 and (copper or "Cu")	USPAT	OR	OFF	2004/10/14 20:49
S7	2209	damas\$4 and (copper or "Cu") and cap\$4	USPAT	OR	OFF	2004/10/14 20:51
S8	0	etching with electrochemicaletching with (copper or "Cu")	USPAT	OR	OFF	2004/10/14 20:52
S9	0	electrochemicaletching with (copper or "Cu")	USPAT	OR	OFF	2004/10/14 20:52
S10	23	electroetching with (copper or "Cu")	USPAT	OR	OFF	2004/10/14 20:56
S11	590	chemical near etching with (copper or "Cu")	USPAT	OR	OFF	2004/10/14 20:57
S12	25337	(electroetching with (copper or "Cu")) an d16	USPAT	OR	OFF	2004/10/14 20:56
S13	1	(electroetching with (copper or "Cu")) and (chemical near etching with (copper or "Cu"))	USPAT	OR	OFF	2004/10/14 20:56

S14	3	chemical near etching with (copper or "Cu") with recess	USPAT	OR	OFF	2004/10/14 21:01
S15	13	chemical near etching with (copper or "Cu") and recess with (copper or "Cu")	USPAT	OR	OFF	2004/10/14 21:43
S16	36	"5380546"	USPAT	OR	OFF	2004/10/14 21:16
S17	185	etching with (copper or "Cu") and recess with (copper or "Cu")	USPAT	OR	OFF	2004/10/14 21:43
S18	20	etching with (copper or "Cu") and recess with (copper or "Cu") and seed\$3 and electroless	USPAT	OR	OFF	2004/10/14 21:51
S19	0	recess with (copper or "Cu") and seeding with (copper or "Cu") and electroless with cap\$4	USPAT	OR	OFF	2004/10/14 21:52
S20	123	nozzle with electroplat\$3	USPAT	OR	OFF	2004/10/14 21:53
S21	6	nozzle with electroplat\$3 and (copper with "Cu")	USPAT	OR	OFF	2004/10/14 21:53
S22	35	nozzle with electroplat\$3 with (metal or alloy)	USPAT	OR	OFF	2004/10/14 21:54
S23	6	nozzle with electroplat\$3 with diameter	USPAT	OR	OFF	2004/10/14 21:56
S24	0	nozzle with electroplat\$3 with diameter and damascene	USPAT	OR	OFF	2004/10/14 21:56
S25	0	nozzle with electroplat\$3 with diameter and (plug or interconnect)	USPAT	OR	OFF	2004/10/14 22:02
S26	542	438/654	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/14 22:14
S27	1710	438/653	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/14 22:41
S28	2040	438/687	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/15 12:28
S29	124	(seed\$3 or seeding or dop\$3 or impurit\$3) with (copper or "Cu") and electroless near plating with cap\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/15 12:30

S30	32	((seed\$3 or seeding or dop\$3 or impurit\$3) with (copper or "Cu") and electroless near plating with cap\$4) and (remov\$3 or etch\$3) with barrier	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/15 12:30
S31	4878	257/758	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/15 14:57
S32	0	(semiconductor or die or chip or Ic) and (dielectric or insulat\$3) and (copper or "Cu") with (plug or via or interconnect\$3 or hole) and barrier with electroplat\$3 with nozzle	USPAT	OR	OFF	2005/03/29 12:22
S33	0	(semiconductor or die or chip or Ic) and (copper or "Cu") with (plug or via or interconnect\$3 or hole) and barrier with electroplat\$3 with nozzle	USPAT	OR	OFF	2005/03/29 12:22
S34	4	(semiconductor or die or chip or Ic) and (copper or "Cu") with (plug or via or interconnect\$3 or hole) and barrier and electroplat\$3 with nozzle	USPAT	OR	OFF	2005/03/29 12:22
S35	378	(semiconductor or die or chip or Ic) and (dielectric or insulat\$3) and (copper or "Cu") with (plug or via or interconnect\$3 or hole) and barrier with select\$5 with deposit\$3	USPAT	OR	OFF	2005/03/30 16:59
S36	145	(semiconductor or die or chip or Ic) and (dielectric or insulat\$3) and (copper or "Cu") with (plug or via or interconnect\$3 or hole) and barrier with selectively with deposit\$3	USPAT	OR	OFF	2005/03/30 17:00
S37	26	(semiconductor or die or chip or Ic) and (dielectric or insulat\$3) and (copper or "Cu") with (plug or via or interconnect\$3 or hole) and barrier with selectively with deposit\$3 same (electrolytic or electroplat\$3 or electroless)	USPAT	OR	OFF	2005/03/30 18:23
S38	5	(semiconductor or die or chip or Ic) and (dielectric or insulat\$3 or damasc\$3) and (copper or "Cu") with (plug or via or interconnect\$3 or hole) and barrier with selectively with deposit\$3 same (electrolytic or electroplat\$3)	USPAT	OR	OFF	2005/03/30 18:24

S39	7	(semiconductor or die or chip or Ic) and (dielectric or insulat\$3 or damasc\$3) and (copper or "Cu") with (plug or via or interconnect\$3 or hole) and (barrier or cap\$4) with selectively with deposit\$3 same (electrolytic or electroplat\$3)	USPAT	OR	OFF	2005/03/30 19:08
S40	75	(semiconductor or die or chip or Ic) and (dielectric or insulat\$3 or damasc\$3) and (copper or "Cu") with (plug or via or interconnect\$3 or hole) and (barrier or cap\$4) with ("Ru" or Ruthenium)	USPAT	OR	OFF	2005/03/30 19:52
S41	15	(semiconductor or die or chip or Ic) and (dielectric or insulat\$3 or damasc\$3) and (copper or "Cu") with (plug or via or interconnect\$3 or hole) and (barrier or cap\$4) with ("Ru" or Ruthenium) same ("Co" or cobalt)	USPAT	OR	OFF	2005/03/30 20:19
S42	0	"6395607".pn. and blanket	USPAT	OR	OFF	2005/03/30 20:59
S43	831	438/652	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/30 21:34
S44	462	438/654	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/30 21:34
S45	1	"6509622".pn. and (transistor or TFT)	USPAT	OR	ON	2005/03/31 17:20
S46	904	438/652	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/18 14:23
S47	490	438/654	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/18 15:15

S48	1696	438/653	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/18 15:36
S49	2441	438/687	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/18 15:57
S50	5008	257/758	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/18 15:57